

# A New Approach to Photocathode Development: From the Recipe to Theory Inspired Design

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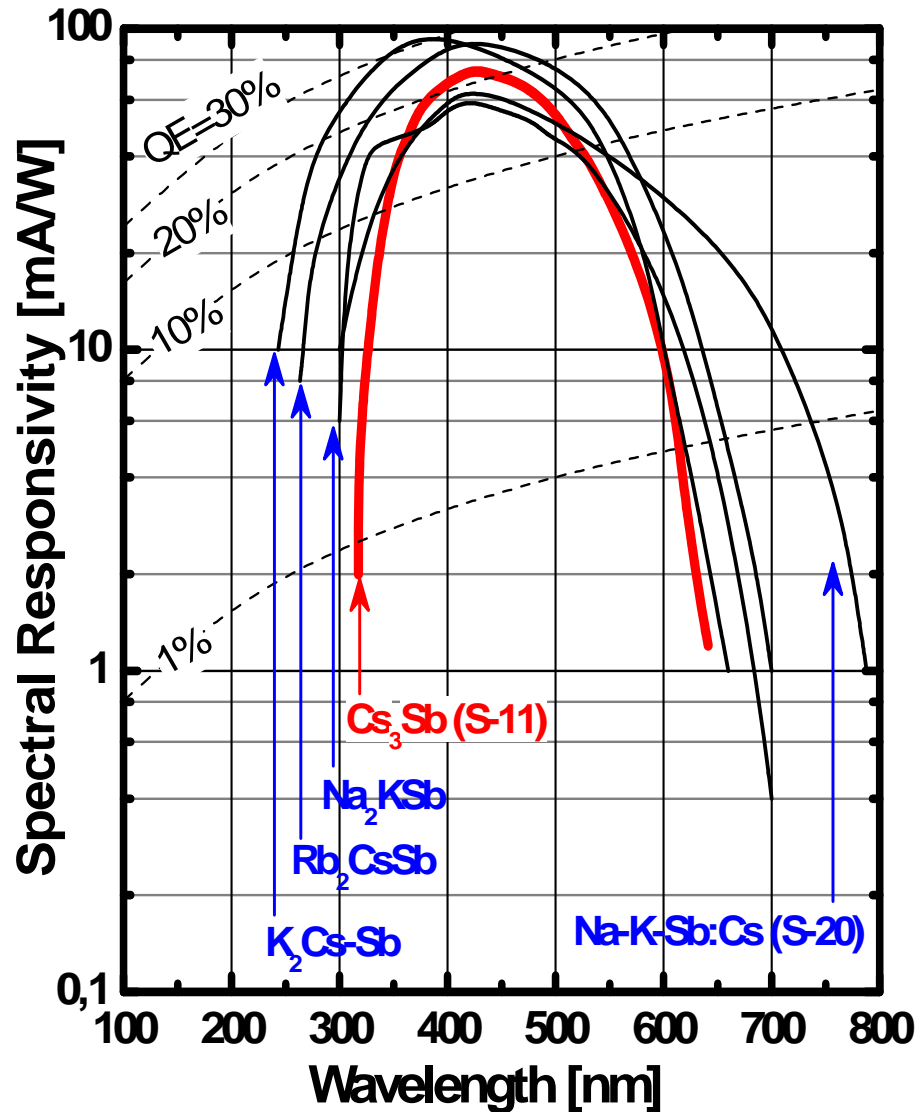
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# Outline

- Motivation
- What is “theory inspired growth”
- X-rays, a tool to visualize the structure of films
- Conclusion



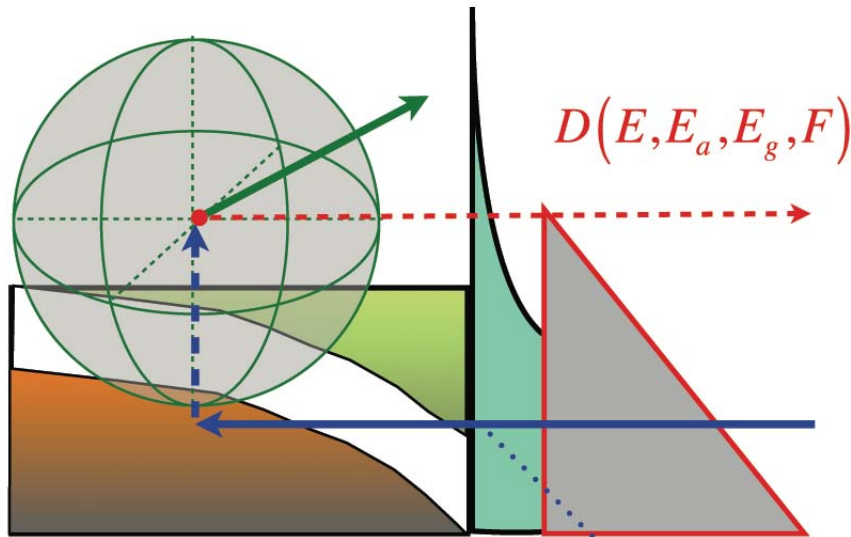
# Selection of Cathode Material



- Multi-alkali are
  - “Obvious” choice in the wavelength range around 400nm
  - Most cost-efficient to produce (Thin-film-technology)
- Selection criteria:
  - Process compatibility
  - Wavelength response
  - Conductivity (large area)
  - High Quantum efficiency
  - Low dark current
  - Robustness (device life time)
- Options:
  - $\text{CsK}_2\text{Sb}$
  - $\text{KNa}_2\text{Sb}$
  - $\text{Cs}_3\text{Sb}$



# What Determines the Quantum Efficiency



Semiconductor

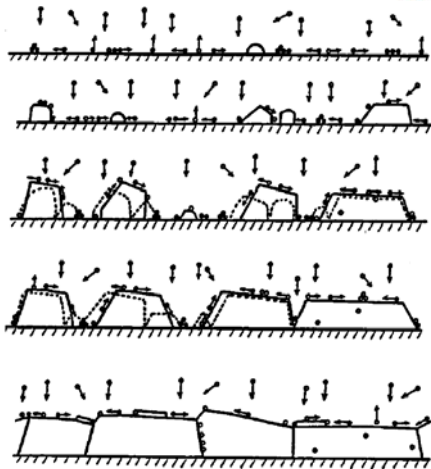
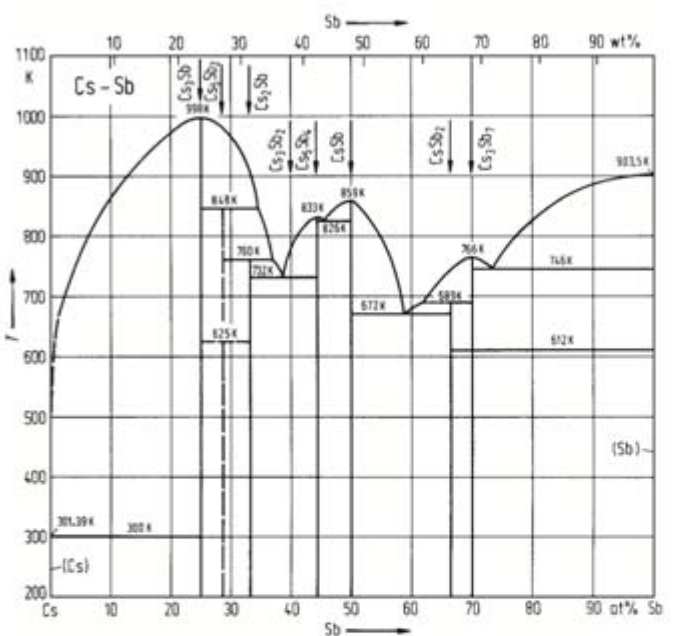


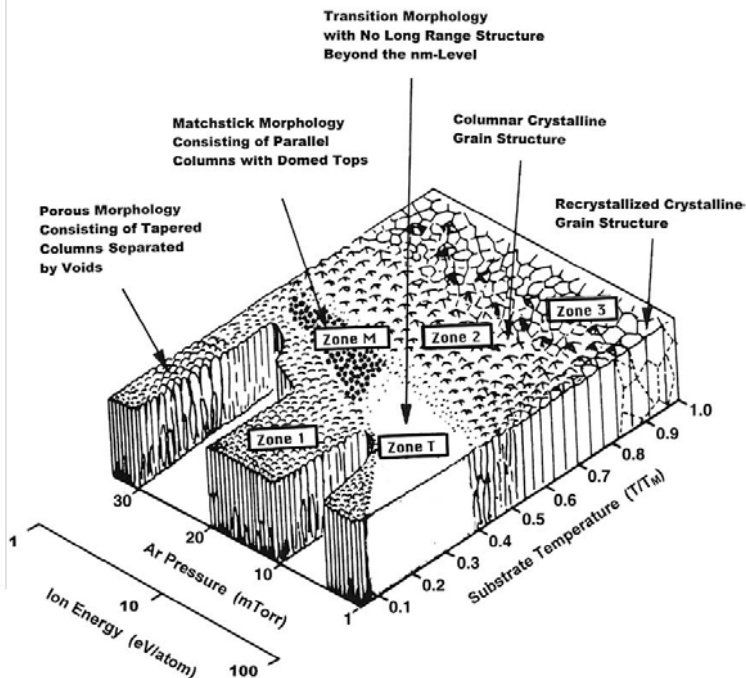
FIG. 1. Schematic diagram illustrating fundamental growth processes controlling microstructural evolution: nucleation, island growth, impingement and coalescence of islands, grain coarsening, formation of polycrystalline islands and channels, development of a continuous structure, and film growth (see Ref. 9).

- Three step model:
  - Absorption
  - Transport to the surface
  - Emission through the surface barrier
  - (reflection losses)
- Ways to manipulate the material:
  - Absorption (band gap & DOS):
    - Band structure by composition variations
  - Transport (scattering):
    - Electron-electron scattering negligible (if not highly doped)
    - Electron-phonon scattering; very difficult to manipulate
    - Electron-impurity scattering; fully growth related
    - Symmetry break (electric fields)
  - Emission properties
    - Surface composition
    - morphology

# A Few Thoughts about Thin-Film Growth



J.H.E. Cartwright et al. / Thin Solid Films 518 (2010) 3422–3427



- Film morphology is responsible for

- Lateral and transversal diffusion rate
- Impurity scattering
- Speciation distribution trough out the film

Recipe parameters and film structure are strongly correlated

Examples for band-gap variations:  $K_3Sb$

Eg: 1.1eV, 1.3eV, 1.4eV (dependent on crystalline phase)



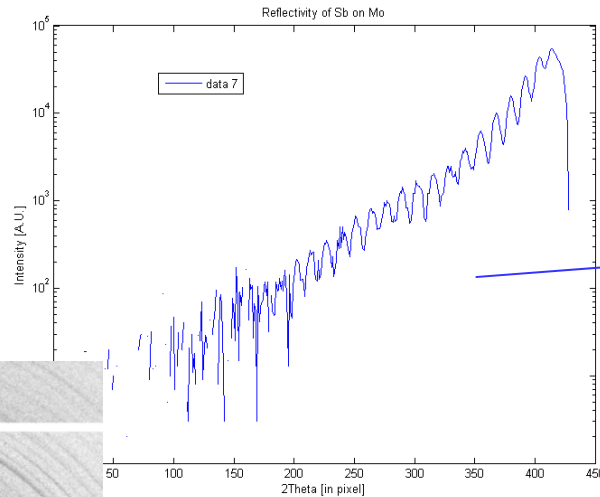
# Roadmap to Optimize Growth Recipe

- **Correlation between functionality and structure**
  - The absorption of photons and generation of photoelectrons
  - The transport of the electrons from the point of generation to the surface
  - The escape from the surface
- **Correlation between Recipe and Structure**
  - Temperature / growth rate
  - Composition of materials
  - Grain size and thickness of the film
- **In - situ Visualization Tool of Microscopic Structure**
  - **X - ray Diffraction:** Crystallographic structure, chemical composition, grain size, crystalline orientation
  - **X - ray Reflectivity:** Control of thickness, various defects, surface roughness

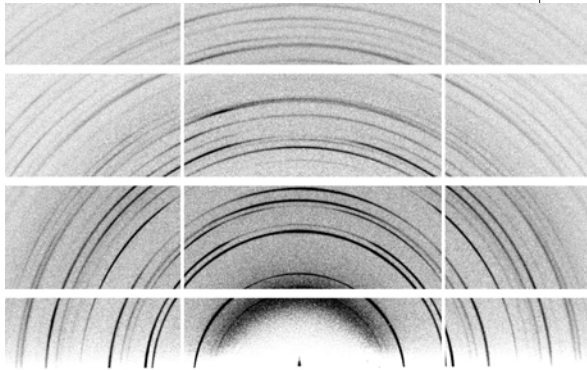


# X-rays, a tool to visualize the structure of films

## In-situ X-ray Scattering



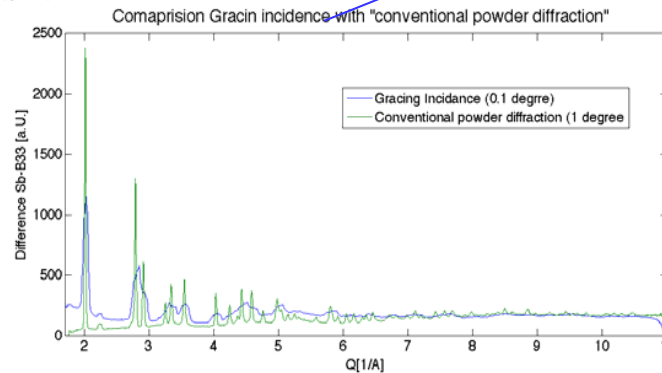
Movie like characterization during the growth:



- Macroscopic film properties
  - Film thickness
  - Roughness
- Microscopic composition
  - Which phases are present
  - Lateral and transversal and homogeneity
  - Crystalline size
  - Preferential crystal growth

Surface composition

- Local workfunction
- Chemical composition

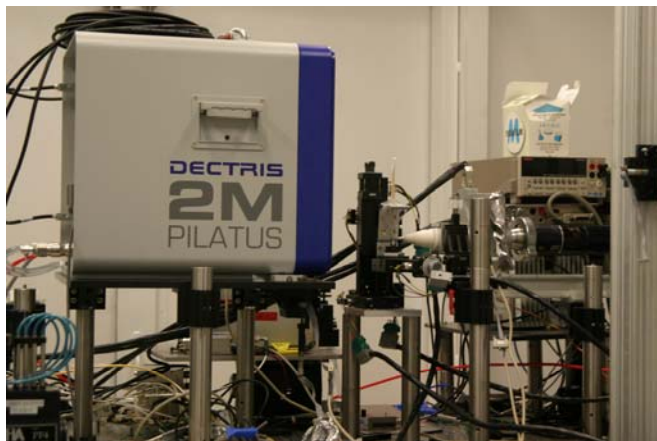


PEEM: collaboration with Howard Padmore (ALS)



# Data-Acquisition & Processing

Azimuthal Integration and fit of peak positions ■

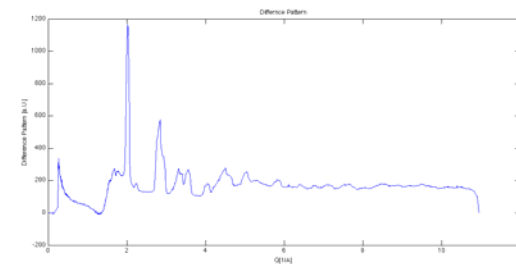
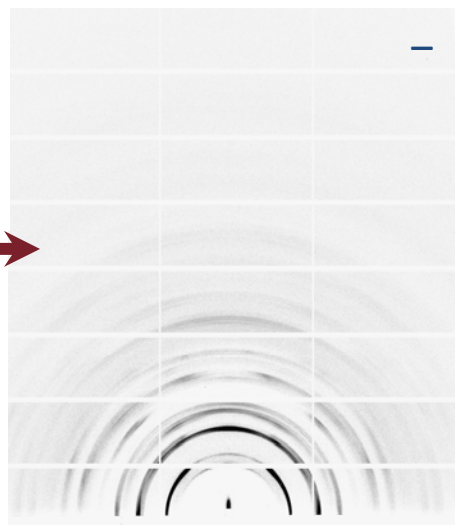
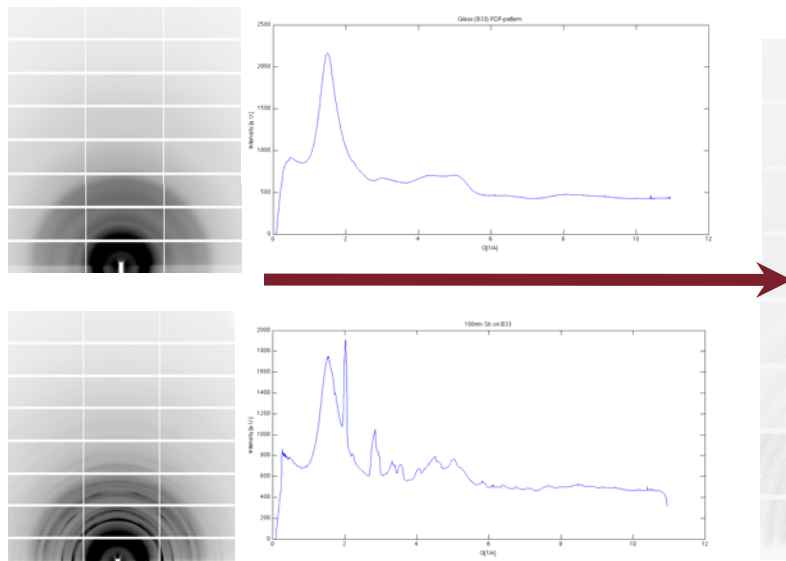


Single shot reveals full structure

- Time resolution  $\sim 100\text{ms}$
- Perfect for insitu experiments
- However: evaporator similar to production condition

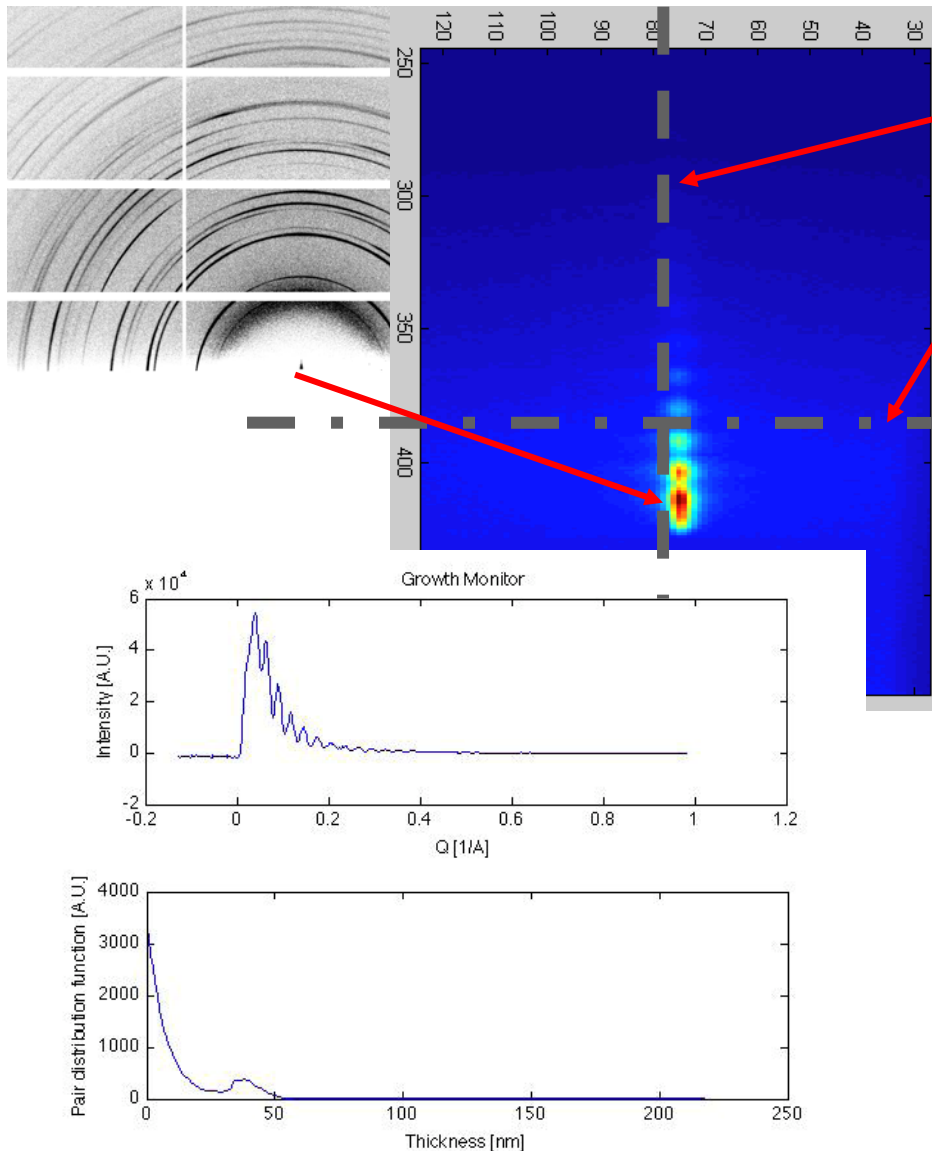
■ Data-Analysis:

- Calibration with known standard ( $\text{CeO}_2$ )
- “Empty”-pattern (B33)
- Sb-on B33 pattern
- Result: Difference showing only Sb-film and changes on glass-substrate





# Thickness Measurement of the Film in Real-Time



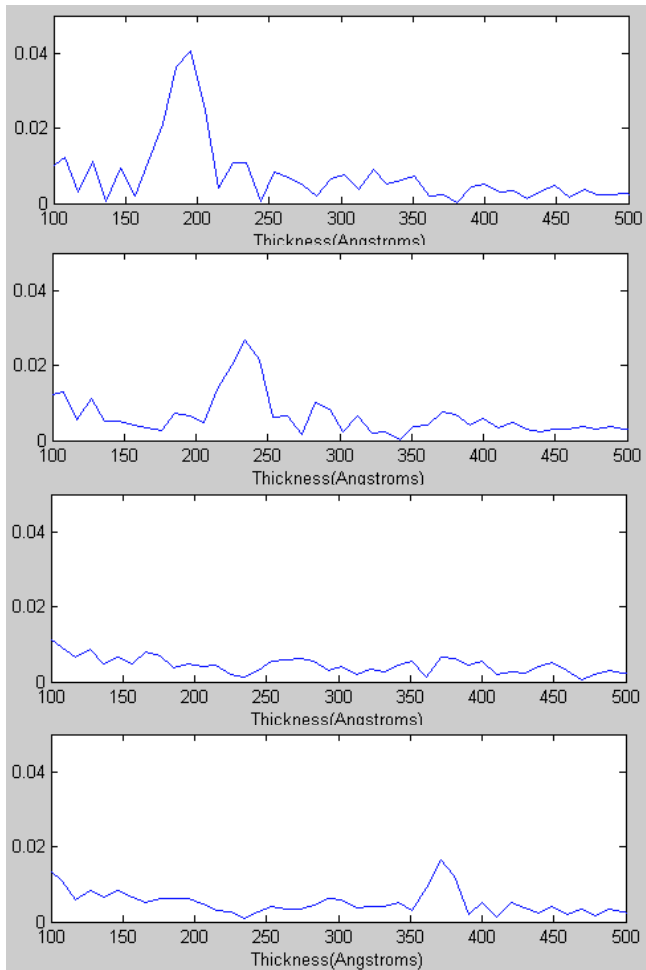
Vertical cut reveals thickness and vertical roughness of film (FFT)

Horizontal cut reveals lateral island-size

- Film thickness and roughness was determined for
  - Sb-fims (different substrate conditions)
  - Sb-film and subsequent K-evaporation
- Currently systematic investigations of
  - different growth conditions
  - surface preparation (interlayer)
- Extracted information (with about 1s time resolution)
  - Thickness
  - Roughness
  - In-plane “partical” size distribution



# K-growth on Sb: One Example (Boing-recipe)



Sb-film (18nm)

K-evaporation started

K-evaporation goes on

Final film

- Sb film starts with about 3 nm (consistent with AFM measurements)
- K-evaporation starts:
  - Roughness is increasing
  - Single peak shows that K instantaneously (1s) reacts and intermixes
- Ongoing evaporation of K:
  - Film shows extreme strong roughness (no peak)
- Final Film:
  - Film roughness decreases with increasing evaporation

Currently in progress: More quantitative analysis and systematic recipe variations



# Crystal growth behavior of Sb-film (Wide Angle X-ray Scattering WAXS)

4-27-2011

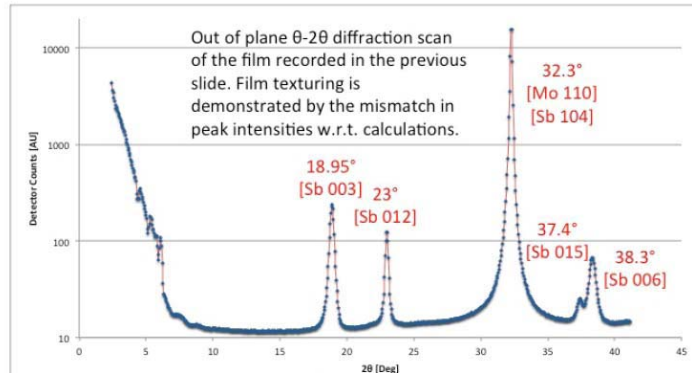
Scan 186: a2scan nu 4 40 zeta 2 20 36 10

Image Center: 271 x 97

Sb Film on Mo Substrate

Thickness: 80 Å (guess)

Deposited at >> 200 °C (guess)



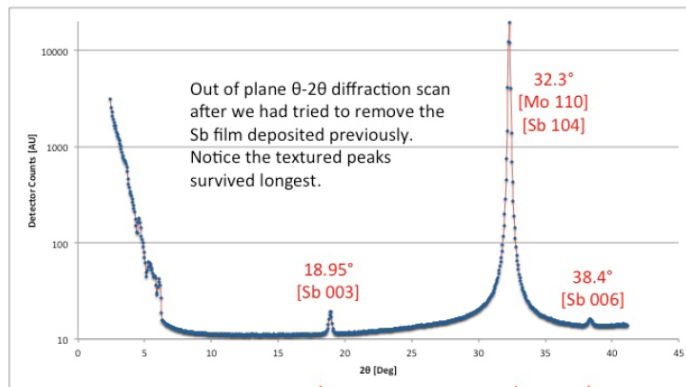
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Scan 189: a2scan nu 4 40 zeta 2 20 36 10

Image Center: 271 x 97

Mo Substrate

w/ residual Sb film



Sb film as deposited

Sb film after heating

- Peak-ratio reveals texturing (pre-orientation of crystallites [Sb 003-orientation])
- After heating:
  - Different crystal orientation show different sticking coefficient
  - Textured crystals “survive” longer

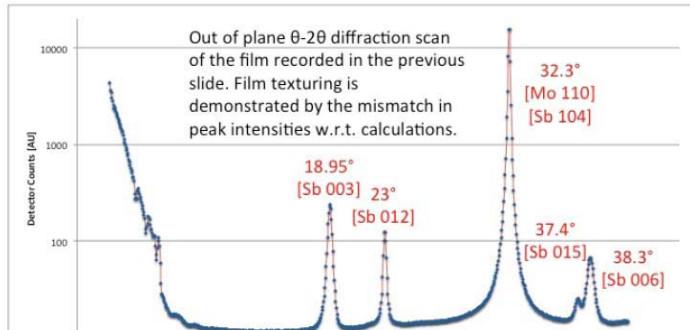
Is multiple applications of heating and evaporations a way to increase the texture and tailor crystal size of the original Sb-film (key to ultra high QE)?



# What Happens after K- and Cs-Evaporation

4-27-2011  
Scan 186: a2scan nu 4 40 zeta 2 20 36 10  
Image Center: 271 x 97

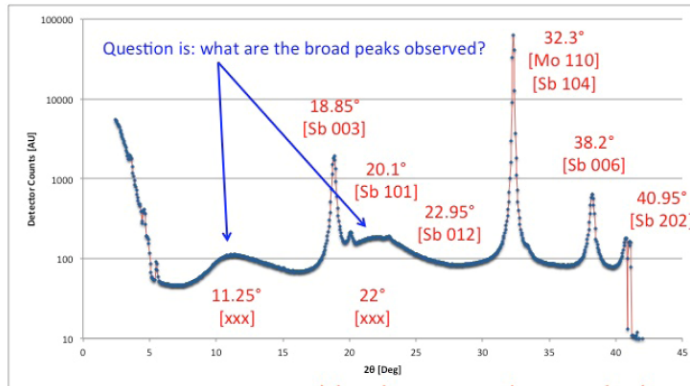
Sb Film on Mo Substrate  
Thickness: 80 Å (guess)  
Deposited at >> 200 °C (guess)



Original Sb-film

4-30-2011 Scan 278  
a2scan nu 4 40 zeta 2 20 36 30  
Image Center: 270 x 96

$K_2CsSb$  Film?  
Thickness: 200 Å Sb + 400 Å of K + 200 Å of Cs (guess)  
Deposited at between 120 - 140 °C, estimated to be ~ 130 °C



Cathode after K- and Cs-Evaporation

- High indexed reflections disappear:
  - Indication that crystallite gets smaller or very strained
- Main reflections show reduced intensity
  - Smaller crystals but still Sb-phase present
- Strong background observable:
  - Not clear which  $Cs_xK_ySb_n$ -phases are produced
  - Is active cathode material in amorphous phase?

Is K- and Cs- reacting on the grain boundaries with strongly increased strain (like Fe-oxidation?)



# Conclusion:

## Is Theory Inspired Growth Possible

- **Correlation between functionality and structure**
  - In principle known
  - Phenomenological model available (no first principle calculations)
- **Correlation between Recipe and Structure**
  - Large parameter space is available
  - Recipe shows strong correlations between individual steps
- **In - situ Visualization Tool of Microscopic Structure**
  - All necessary microscopic film parameters can be visualized in real time

The next big steps:

- Proof of principle has been performed and shown.
- Understanding correlations between process parameters and microscopic structures of known recipes.
- Developing new strategies in thin-film technology to create high quantum efficiency cathodes.

